



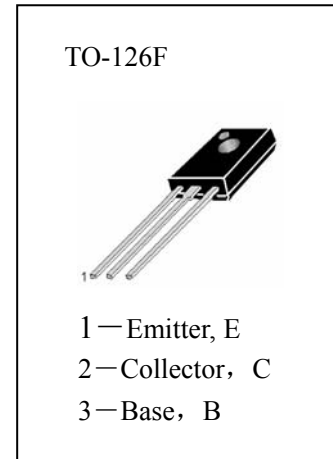
HBD682

APPLICATIONS

Medium Power Linear switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-65~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation (T _c =25°C)	40W
V _{CBO}	Collector-Base Voltage	-100V
V _{CEO}	Collector-Emitter Voltage	-100V
V _{EBO}	Emitter-Base Voltage	-5V
I _C	Collector Current (Pulse)	-6A
I _C	Collector Current (DC)	-4A
I _B	Base Current	-100mA



电参数 (ELECTRICAL CHARACTERISTICS (T_a=25°C))

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector Cut-off Current			-200	μ A	V _{CB} =-100V, I _E =0
I _{EBO}	Emitter Cut-off Current			-2	mA	V _{EB} =-5V, I _C =0
I _{CES}	Collector Cut-off Current			-500	μ A	V _{CE} =-100V, V _{EB} =0
*H _{FE}	DC Current Gain	750				V _{CE} =-3V, I _C =-1.5mA
*V _{CE(sat)}	Collector- Emitter Saturation Voltage			-2.5	V	I _C =-1.5A, I _B =-30mA
V _{BE(on)}	Base-Emitter On Voltage			-2.5	V	V _{CE} =-3V, I _C =-1.5A
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	-100				I _C =-50mA, I _B =0

* Pulse Test:PW=300μS,Duty Cycle=1.5% Pulsed

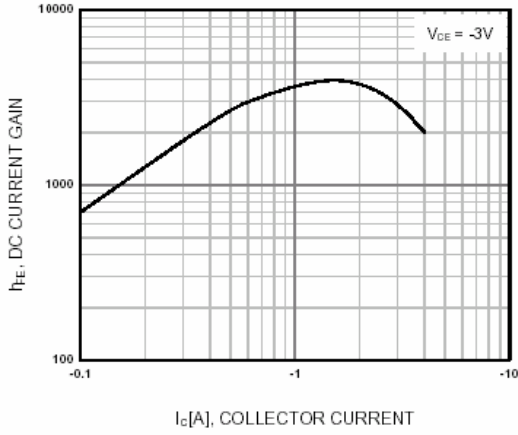
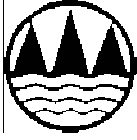


Figure 1. DC current Gain

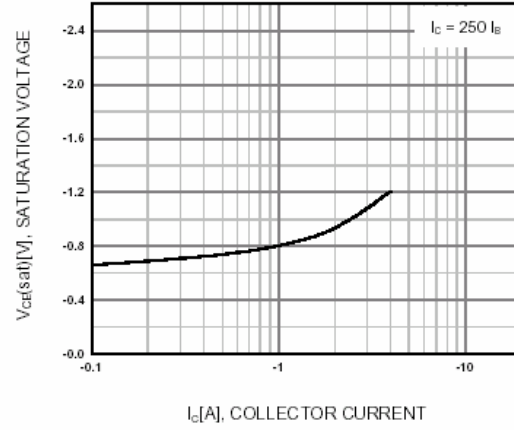


Figure 2. Collector-Emitter Saturation Voltage

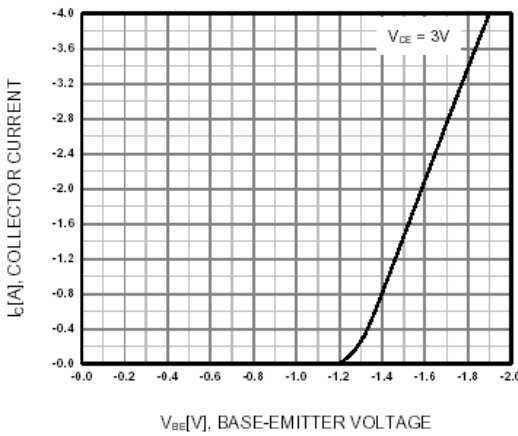


Figure 3. Base-Emitter On Voltage

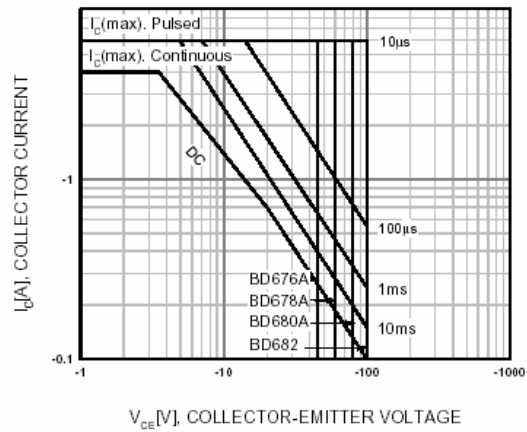


Figure 4. Safe Operating Area

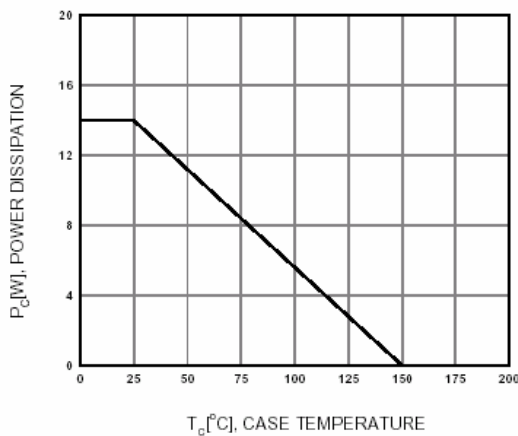


Figure 5. Power Derating